MARKED-UP COPY OF AMENDMENTS

IN RE APPLICATION OF:

.

ATSUSHI SHIOTA ET AL.

: GROUP ART UNIT: 1712

SERIAL NO: 09/770,289

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FILED: JANUARY 29, 2001

: EXAMINER: FEELY, M.

FOR: PROCESS FOR PRODUCING

SILICA-BASED FILM, SILICA-BASED FILM, INSULATING FILM, AND SEMICONDUCTOR DEVICE

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated February 28, 2002, please amend the application identified above as follows (marked-up copy of amendments attached):

IN THE CLAIMS

Please amend Claims 1, 3 and 6 as follows:

1. (Amended) A process for producing a silica-based film [which comprises], the process comprising irradiating a film comprising at least one siloxane compound with electron beams at an irradiation dose of from 1 to 500 μC cm² to thereby convert the film into a film having a dielectric constant of 3 or lower and having silicon carbide bonds represented by Si-C-Si.

3. (Amended) The process as claimed in claim 1, wherein the siloxane compound is a product of the hydrolysis and or condensation of at least one compound selected from the group consisting of compounds represented by the following formula (1):

$$R^{1}_{\alpha}Si(OR^{2})_{4,\alpha} \tag{1}$$

wherein R^1 represents a monovalent organic group or a hydrogen atom; R^2 represents a monovalent organic group; and a [Is] is an integer of 0 to 2,

and compounds represented by the following formula (2):

$$R_{b}^{3}(R^{4}O)_{3-b}Si-(R^{7})_{d}-Si(OR^{5})_{3-c}R_{c}^{6}$$
(2)

wherein R^3 , R^4 , R^5 , and R^6 may be the same or different and each represents a monovalent organic group; b and c may be the same or different and each is an integer of 0 to 2; R^7 represents an oxygen atom or a group represented by -(CH₂)_n-, wherein n is 1 to 6; and d is 0 or 1.

6. (Amended) The process as claimed in claim 1, wherein the electron beam irradiation is conducted at an energy of from 0.1 to 50 keV [in an irradiation dose of from 1 to 1,000 μ C/cm²].

Please add new Claims 16 as follows:

--16. (New) The process as claimed in claim 1, wherein the irradiation dose is from 1 to $200~\mu\text{C/cm}^2$.--